

Amendments to the Specification:

Please amend the specification as follows:

Please replace the paragraph starting at page 3, line 17 with the following rewritten paragraph:

This LED 20 is a red LED having an emission wavelength of around 630 nm and which is prepared by lamination of an n-type GaAs substrate 1, an n-type (selenium (Se) doped) $(Al_{0.7}Ga_{0.3})_{0.5}In_{0.5}P$ cladding layer 2, an undoped $(Al_{0.15}Ga_{0.85})_{0.5}In_{0.5}P$ active layer 3, a p-type (Zn doped) $(Al_{0.7}Ga_{0.3})_{0.5}In_{0.5}P$ cladding layer 4 having $5 \times 10^{17} \text{ cm}^{-3}$ Zn concentration, a p-type GaP layer 5, a p-type InP layer 6 [[6A]], a transparent conductive film 7, an n-type electrode 8 formed on the whole surface of the bottom of a chip, and a p-type circular electrode 9 having a 150 μm diameter and formed on the top of the LED.

Please replace the paragraph starting at page 4, line 12 with the following rewritten paragraph:

The p-type InP layer 6 [[6A]] is formed at $1 \times 10^{18} \text{ cm}^{-3}$ Zn concentration and which is provided as an underlying layer of the transparent conductive film 7, functioning to prevent exfoliation of the transparent conductive film 7 from an epitaxial wafer in case of dicing and the like.

Please replace the paragraph starting at page 5, line 2 with the following rewritten paragraph:

The LED 20 is fabricated by cutting out an epitaxial wafer with electrodes used for the LED formed in the above-described structure into 300 μm square chip size according to dicing. In a process for dicing and the like, the transparent conductive film 7 is cut out while maintaining adherence to the p-type InP layer 6 [[6A]]. The LED 20 is die-bonded on the TO-18 stem, and the LED 20 is electrically connected to the TO-18 stem by wire-bonding.

Please replace the paragraph starting at page 5, line 10 with the following rewritten paragraph:

According to the above-described conventional LED, however, a junction of the LED having pn junction and the transparent conductive film 7 becomes substantially npn, resulting in an appearance of series resistance due to barrier in the interface of the transparent conductive film 7 and the p-type InP layer 6 [[6A]]. In this respect, since the Zn concentration ($1 \times 10^{18} \text{ cm}^{-3}$) in the above-described transparent conductive film 7 is insufficient for an amount of reducing series resistance, a high operative voltage is required in light emission. Besides, a thickness (30 nm) for acquiring sufficient current spreading characteristics is required, so that there is a problem of appearing hindrance for attaining high luminance.